

MOSFETs Silicon N-channel MOS (U-MOSVIII-H)

XPH3R206NC

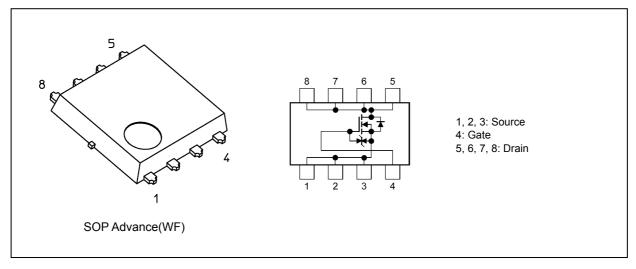
1. Applications

- · Automotive
- · Motor Drivers
- · Switching Voltage Regulators

2. Features

- (1) AEC-Q101 qualified
- (2) Small, thin package
- (3) Low drain-source on-resistance: $R_{DS(ON)} = 2.6 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (4) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 60 \text{ V)}$
- (5) Enhancement mode: V_{th} = 1.5 to 2.5 V (V_{DS} = 10 V, I_{D} = 0.5 mA)

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V_{DSS}	60	V
Gate-source voltage			V_{GSS}	±20	
Drain current (DC)		(Note 1)	I _D	70	Α
Drain current (pulsed)		(Note 1)	I _{DP}	210	
Power dissipation	(T _c = 25 °C)		P_{D}	132	W
Power dissipation	(t = 10 s)	(Note 2)]	3.0	
Power dissipation	(t = 10 s)	(Note 3)	1	0.96	
Single-pulse avalanche energy		(Note 4)	E _{AS}	147	mJ
Single-pulse avalanche current			I _{AS}	70	Α
Channel temperature		(Note 5)	T _{ch}	175	°C
Storage temperature		(Note 5)	T _{stg}	-55 to 175	

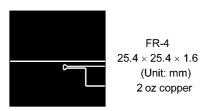
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

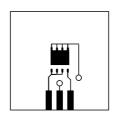
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal impedance	(T _c = 25 °C)		Z _{th(ch-c)}	1.13	°C/W
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 2)	Z _{th(ch-a)}	50	
Channel-to-ambient thermal impedance	(t = 10 s)	(Note 3)	Z _{th(ch-a)}	156	

- Note 1: Ensure that the channel temperature does not exceed 175 °C.
- Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1
- Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2
- Note 4: V_{DD} = 48 V, T_{ch} = 25 °C (initial), L = 23.1 μ H, R_G = 25 Ω , I_{AS} = 70 A
- Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.





FR-4 $25.4 \times 25.4 \times 1.6$ (Unit: mm) 2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cut-off current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	60	_	_	٧
	V _{(BR)DSX}	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	40	_	_	
Gate threshold voltage	V_{th}	$V_{DS} = 10 \text{ V}, I_{D} = 0.5 \text{ mA}$	1.5	_	2.5	
Drain-source on-resistance	R _{DS(ON)}	$V_{GS} = 4.5 \text{ V}, I_D = 35 \text{ A}$	_	3.9	6.2	mΩ
		V_{GS} = 10 V, I_D = 35 A		2.6	3.2	

6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	4180	_	pF
Reverse transfer capacitance	C _{rss}		_	180	_	
Output capacitance	C _{oss}		_	2050	_	
Gate resistance	r _g		_	2.5	5.0	Ω
Switching time (rise time)	t _r	See Fig. 6.2.1	_	20	_	ns
Switching time (turn-on time)	t _{on}		_	40	_	
Switching time (fall time)	t _f		_	19	_	
Switching time (turn-off time)	t _{off}		_	88	_	

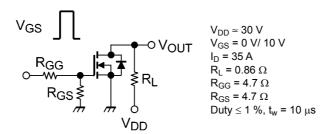


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx 48 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 70 \text{ A}$	-	65	1	nC
Gate-source charge 1	Q _{gs1}			17		
Gate-drain charge	Q_{gd}			10	_	

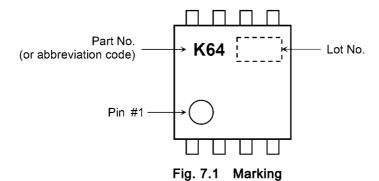
6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (N	ote 6)	I _{DRP}	_	_	_	210	Α
Diode forward voltage		V_{DSF}	I _{DR} = 70 A, V _{GS} = 0 V	_	_	-1.2	V

Note 6: Ensure that the channel temperature does not exceed 175 °C.



7. Marking





8. Characteristics Curves (Note)

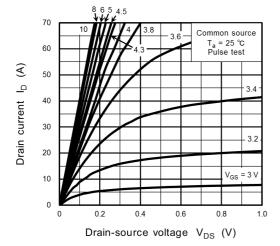


Fig. 8.1 I_D - V_{DS}

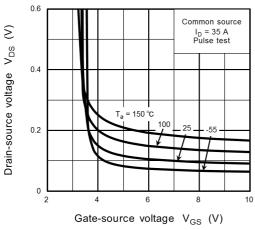


Fig. 8.3 V_{DS} - V_{GS}

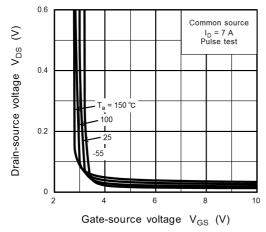


Fig. 8.5 V_{DS} - V_{GS}

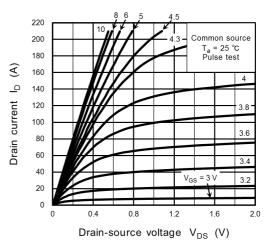


Fig. 8.2 I_D - V_{DS}

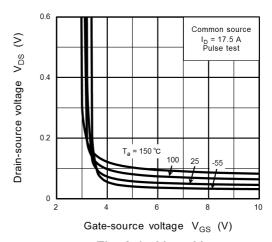


Fig. 8.4 VDS - VGS

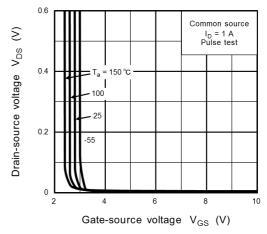


Fig. 8.6 $V_{DS} - V_{GS}$



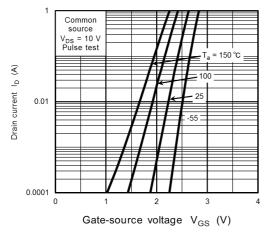


Fig. 8.7 ID - VGS

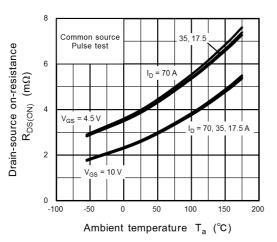


Fig. 8.9 RDS(ON) - Ta

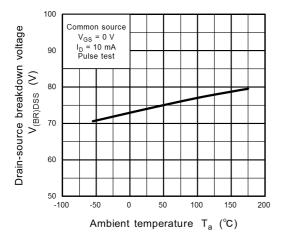


Fig. 8.11 V_{(BR)DSS} - T_a

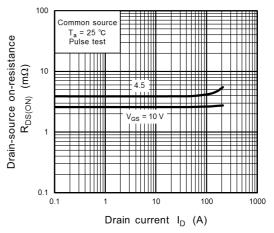


Fig. 8.8 R_{DS(ON)} - I_D

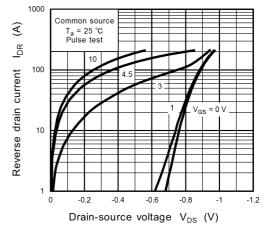


Fig. 8.10 I_{DR} - V_{DS}

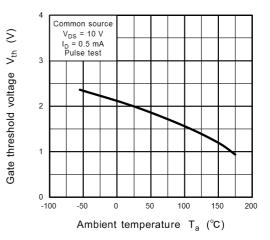


Fig. 8.12 V_{th} - T_a



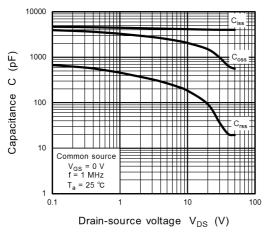


Fig. 8.13 Capacitance - V_{DS}

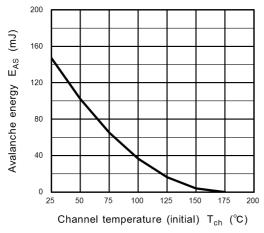


Fig. 8.15 E_{AS} - T_{ch}(Guaranteed Maximum)

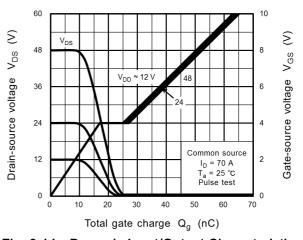


Fig. 8.14 Dynamic Input/Output Characteristics

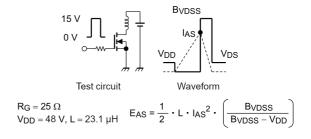


Fig. 8.16 Test Circuit/Waveform



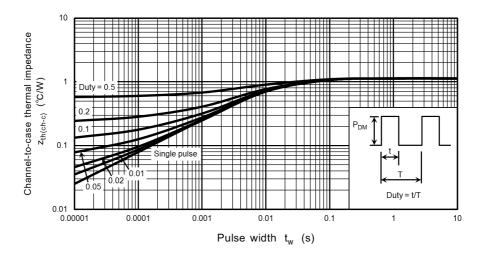
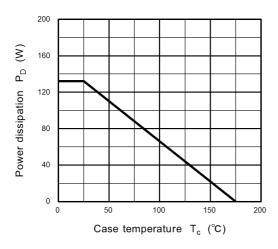


Fig. 8.17 $z_{th(ch-c)} - t_w$ (Guaranteed Maximum)



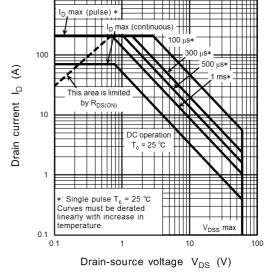


Fig. 8.18 P_D - T_c (Guaranteed Maximum)

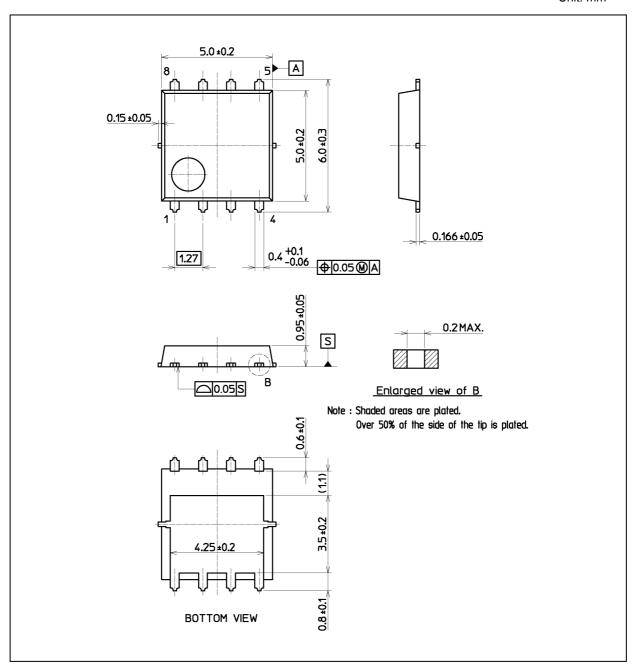
Fig. 8.19 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.080 g (typ.)

Package Name(s)
TOSHIBA: 2-5Q4A
Nickname: SOP Advance(WF)



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